

AMENDMENTS TO THE CLAIMS:

Claims 1-4 (cancelled)

5. (New) A plating method comprising:
providing a substrate having fine trench patterns which are covered with a seed layer;
disposing said substrate adjacent an anode such that said substrate and said anode face one another and define a plating space therebetween;
disposing a plating liquid impregnation material in said plating space such that a gap is formed between said substrate and said plating liquid impregnation material;
supplying a plating liquid into said plating space; and
forming a plated film on a surface of said seed layer by
(i) applying an electric current between said substrate and said anode without bringing said substrate into contact with said plating liquid impregnation material, and
(ii) moving a portion of said substrate facing said plating liquid impregnation material, relative to said anode, in such a manner that an inner central portion of the surface of said seed layer faces said plating liquid impregnation material for a longer period of time than does an outer peripheral portion of the surface of said seed layer.

6. (New) The plating method according to claim 5, wherein
moving a portion of said substrate, facing said plating liquid impregnation material, relative to said anode comprises relatively moving said portion of said substrate by rotating said substrate.

7. (New) The plating method according to claim 5, wherein
moving a portion of said substrate, facing said plating liquid impregnation material, relative to said anode comprises relatively moving said portion of said substrate by rotating said anode.

8. (New) The plating method according to claim 5, wherein
moving a portion of said substrate, facing said plating liquid impregnation material, relative to said anode comprises relatively moving said portion of said substrate by translating said anode.